74AUP1G07 Low-power buffer with open-drain output Rev. 7 — 16 July 2012

Product data sheet

1. General description

The 74AUP1G07 provides the single non-inverting buffer with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt-trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \ \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



Low-power buffer with open-drain output

3. Ordering information

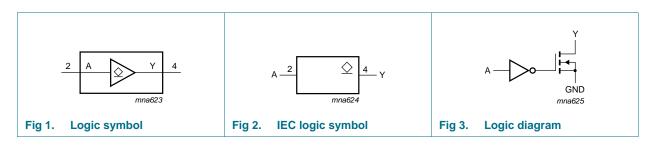
Table 1. Ordering	g information							
Type number	Package							
	Temperature range	Name	Description	Version				
74AUP1G07GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				
74AUP1G07GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886				
74AUP1G07GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891				
74AUP1G07GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74AUP1G07GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202				
74AUP1G07GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226				

4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP1G07GW	pS
74AUP1G07GM	pS
74AUP1G07GF	pS
74AUP1G07GN	pS
74AUP1G07GS	pS
74AUP1G07GX	pS

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

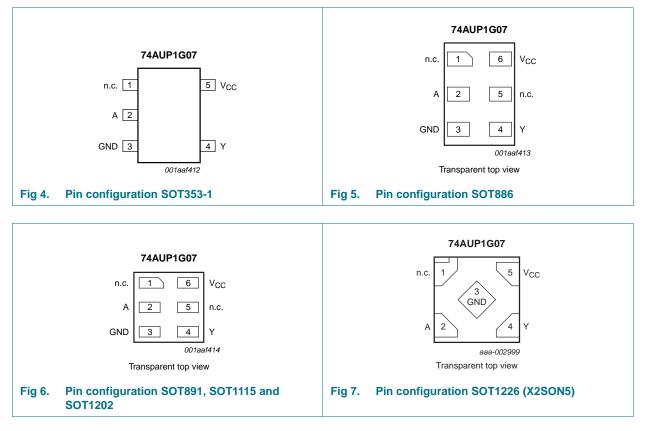


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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description								
Symbol	Pin		Description					
	TSSOP5 and X2SON5	XSON6						
n.c.	1	1	not connected					
A	2	2	data input					
GND	3	3	ground (0 V)					
Y	4	4	data output					
n.c.	-	5	not connected					
V _{CC}	5	6	supply voltage					

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7. Functional description

Table 4. Function table	Table 4.	Function table ^[1]
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Input	Output
A	Y
L	L
Н	Z

[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
Ι _{ΟΚ}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2]	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
 For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Recommended	operating	conditions
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Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	0	200	ns/V

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbo	I Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	25 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70 \times V_{\text{CC}}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3\times V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{OZ}	OFF-state output current	$V_{I} = V_{IH}$; $V_{O} = 0 V$ to 3.6 V; $V_{CC} = 0 V$ to 3.6 V	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μΑ
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	0.5	μΑ
∆l _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.8	-	pF
Co	output capacitance	output enabled; $V_0 = GND$; $V_{CC} = 0 V$	-	1.7	-	pF
		output disabled; $V_0 = GND$; $V_{CC} = 0 V$	-	1.1	-	pF
T _{amb} = ·	–40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 \text{ V} \text{ to } 1.95 \text{ V}$	$0.65 \times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
VIL	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
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NXP Semiconductors

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Low-power buffer with open-drain output

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		I_0 = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		I_0 = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.33	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
l _{oz}	OFF-state output current	$V_{\rm I}$ = $V_{\rm IH};$ $V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.5	μA
I _{OFF}	power-off leakage current	$V_{I} \text{ or } V_{O}$ = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_{1} \text{ or } V_{0} = 0 \text{ V to } 3.6 \text{ V};$		±0.6	μA	
I _{CC}	supply current			0.9	μA	
∆l _{CC}	additional supply current	V_{I} = V_{CC} – 0.6 V; I_{O} = 0 A; V_{CC} = 3.3 V	-	-	50	μΑ
T _{amb} = –	40 °C to +125 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.75 \times V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70\times V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25\times V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30\times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I_{O} = 1.1 mA; V_{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		I_{O} = 1.7 mA; V_{CC} = 1.4 V	-	-	0.41	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
lı	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
l _{oz}	OFF-state output current	$V_{\rm I}$ = $V_{\rm IH};$ $V_{\rm O}$ = 0 V to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.75	μA
I _{OFF}	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±0.75	μA

Table 7. Static characteristics ... continued

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At recom	mended operating condition	s; voltages are referenced to GND (ground	= 0 V).			
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = 0 \ \text{A}; \\ V_{CC} = 0.8 \ \text{V to } 3.6 \ \text{V} \end{array}$	-	-	1.4	μA
ΔI_{CC}	additional supply current	V_{I} = V_{CC} – 0.6 V; I_{O} = 0 A; V_{CC} = 3.3 V	-	-	75	μA

Table 7. Static characteristics ... continued

11. Dynamic characteristics

Table 8. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions			25 °C		-4	0 °C to +1	25 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	11.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V}$ to 1.3 V		2.1	4.1	7.5	1.7	9.1	10.0	ns
		V_{CC} = 1.4 V to 1.6 V		1.6	3.0	5.1	1.3	6.1	6.7	ns
		V_{CC} = 1.65 V to 1.95 V		1.6	2.7	4.0	1.2	5.0	5.5	ns
		V_{CC} = 2.3 V to 2.7 V		1.1	2.1	3.2	0.9	4.0	4.4	ns
		V_{CC} = 3.0 V to 3.6 V		1.4	2.2	2.8	1.1	3.3	3.6	ns
C _L = 10	pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	14.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$		3.0	5.1	9.0	2.4	11.2	12.3	ns
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		2.3	3.8	6.1	2.0	7.4	8.1	ns
		V_{CC} = 1.65 V to 1.95 V		2.4	3.6	4.8	1.8	6.1	6.7	ns
		V_{CC} = 2.3 V to 2.7 V		1.7	2.8	3.8	1.3	4.8	5.3	ns
		V_{CC} = 3.0 V to 3.6 V		2.2	3.1	4.2	1.6	4.5	5.0	ns
C _L = 15	pF									
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		V _{CC} = 0.8 V		-	17.7	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$		3.5	6.1	10.4	3.2	13.1	14.5	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V		3.0	4.5	6.8	2.6	8.6	9.4	ns
		V _{CC} = 1.65 V to 1.95 V		2.8	4.4	6.7	2.2	7.8	8.6	ns
		V_{CC} = 2.3 V to 2.7 V		2.4	3.4	4.5	1.9	5.3	5.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		2.2	4.0	5.7	1.9	6.1	6.7	ns

Low-power buffer with open-drain output

Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C		Unit		
				Min	Typ <mark>[1]</mark>	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 30	pF							•		
t _{pd}	propagation delay	A to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 V$		-	24.6	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V		4.8	9.0	15.6	4.3	18.8	20.7	ns
		V_{CC} = 1.4 V to 1.6 V		4.1	6.7	9.4	3.7	11.8	13.0	ns
		V_{CC} = 1.65 V to 1.95 V		3.8	6.8	9.7	3.2	11.0	12.1	ns
		V_{CC} = 2.3 V to 2.7 V		3.7	5.2	6.7	3.0	7.1	7.8	ns
		V_{CC} = 3.0 V to 3.6 V		3.6	6.4	9.7	2.8	10.4	11.4	ns
C _L = 5 p	F, 10 pF, 15 pF and	30 pF								
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz};$ V _I = GND to V _{CC}	[3]							
		$V_{CC} = 0.8 V$		-	0.5	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V		-	0.6	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V		-	0.6	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V		-	0.7	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	0.9	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	1.2	-	-	-	-	pF

Table 8. Dynamic characteristics ... continued

t circuit o Valu to CND ($d = 0 V \cdot f_{0}$ Ei. 0

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 P_{D} = $C_{PD} \times V_{CC}{}^{2} \times f_{i} \times N$ where:

 f_i = input frequency in MHz;

 V_{CC} = supply voltage in V;

N = number of inputs switching.

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12. Waveforms

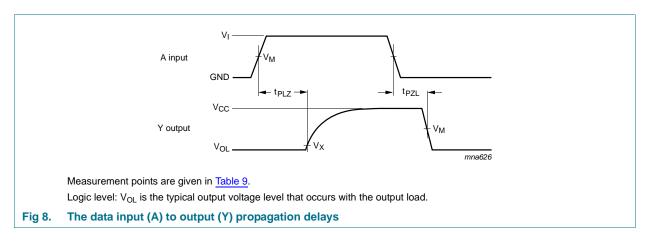


Table 9. Measurement points

Supply voltage	Input	Output	
V _{CC}	V _M	V _M	Vx
0.8 V to 1.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.1 V
1.65 V to 2.7 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.15 V
3.0 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{OL} + 0.3 V

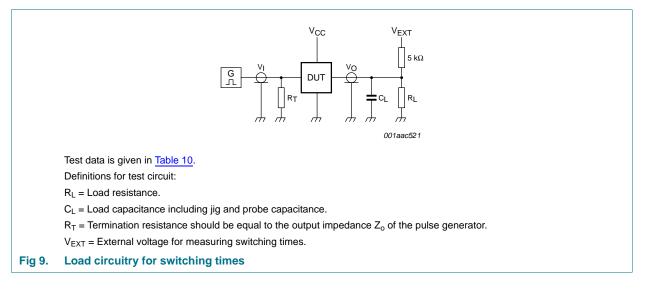


Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	RL ^[1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times, $R_L = 5 k\Omega$, for measuring propagation delays, setup and hold times and pulse width, $R_L = 1 M\Omega$.

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13. Package outline

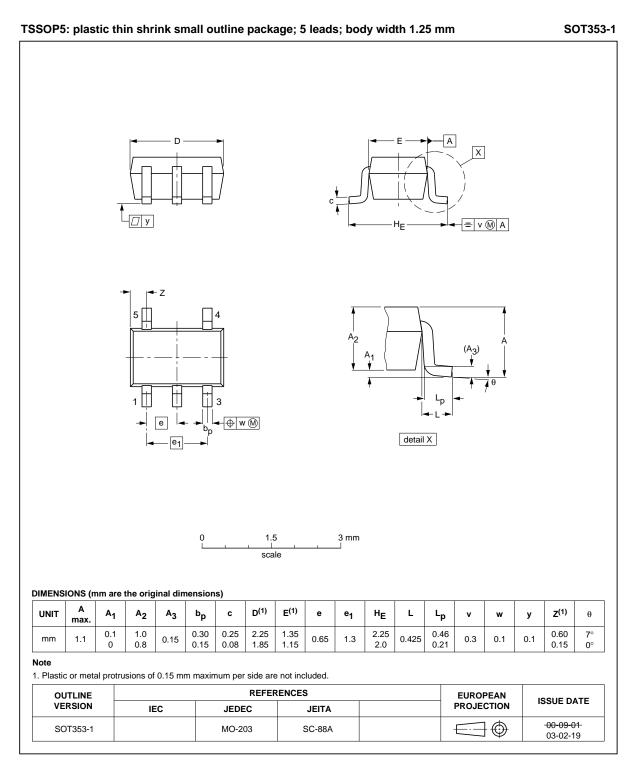


Fig 10. Package outline SOT353-1 (TSSOP5)

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Low-power buffer with open-drain output

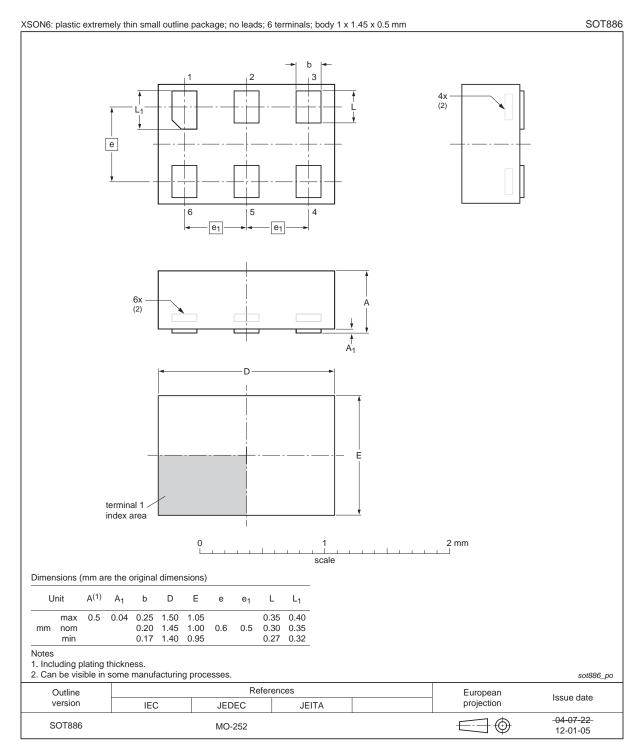


Fig 11. Package outline SOT886 (XSON6)

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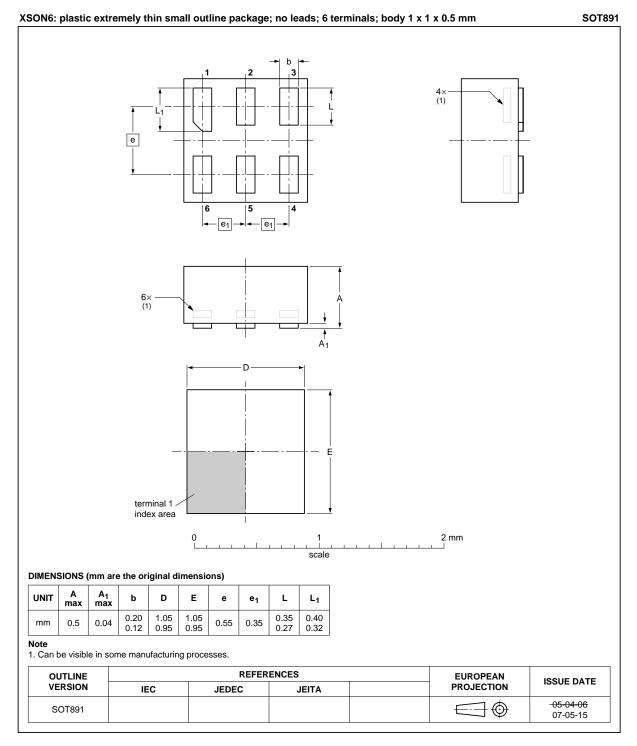
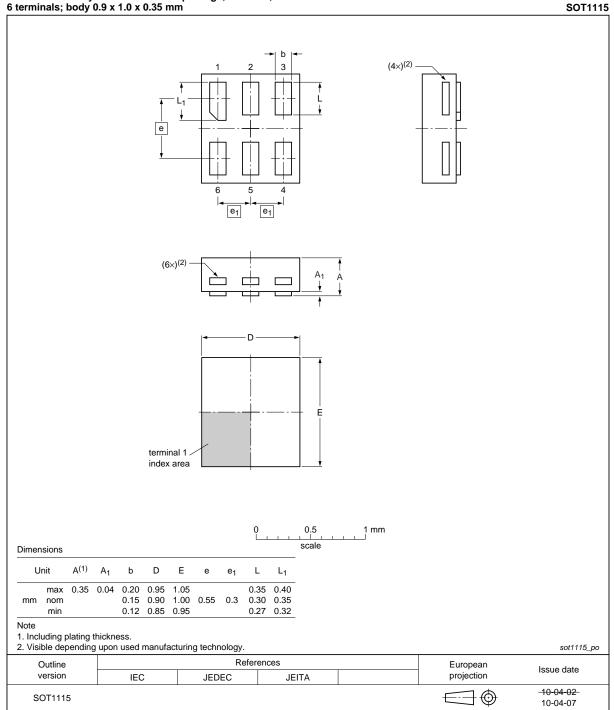


Fig 12. Package outline SOT891 (XSON6)

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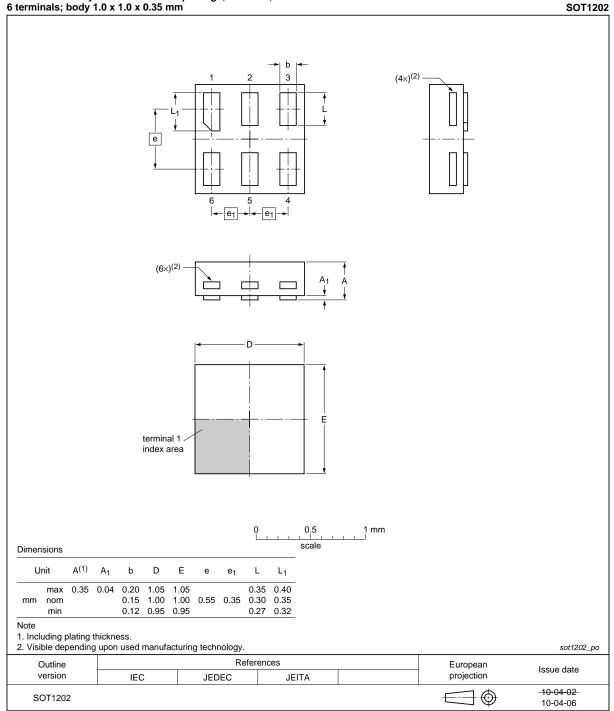


XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 13. Package outline SOT1115 (XSON6)

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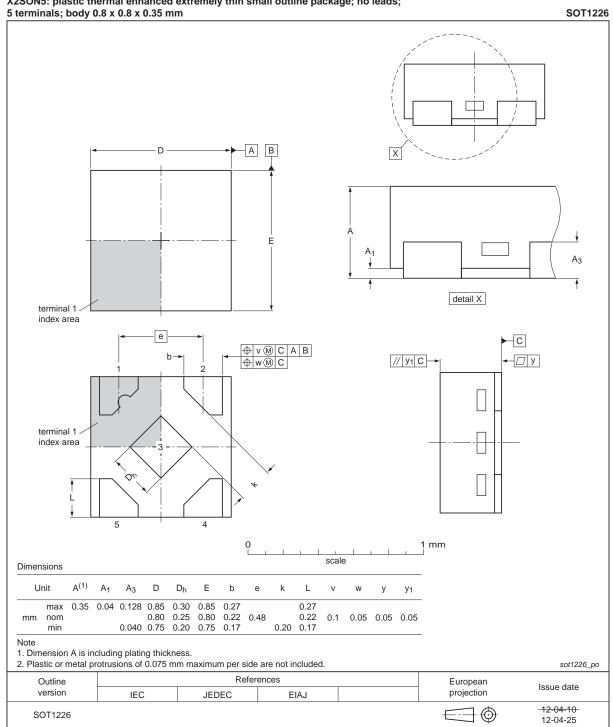
XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 14. Package outline SOT1202 (XSON6)

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X2SON5: plastic thermal enhanced extremely thin small outline package; no leads;

Fig 15. Package outline SOT1226 (X2SON5)

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14. Abbreviations

Table 11. Abbreviations				
Acronym	Description			
CDM	Charged Device Model			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			
-				

15. Revision history

Table 12.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G07 v.7	20120716	Product data sheet	-	74AUP1G07 v.6
Modifications:	 Package ou 	Itline drawing of SOT1226	(Figure 15) modified.	
74AUP1G07 v.6	20120412	Product data sheet	-	74AUP1G07 v.5
Modifications:	 Added type 	number 74AUP1G07GX (SOT1226)	
	 Package ou 	Itline drawing of SOT886 (Figure 11) modified.	
74AUP1G07 v.5	20111115	Product data sheet	-	74AUP1G07 v.4
Modifications:	 Legal pages 	s updated.		
74AUP1G07 v.4	20100902	Product data sheet	-	74AUP1G07 v.3
74AUP1G07 v.3	20090617	Product data sheet	-	74AUP1G07 v.2
74AUP1G07 v.2	20070614	Product data sheet	-	74AUP1G07 v.1
74AUP1G07 v.1	20061010	Product data sheet	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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